

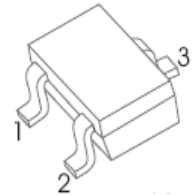
TRANSISTOR(PNP)

FEATURES

- High DC Current Gain
- High Voltage and High Current.
- Complementary to 2SC4116
- Small Package

APPLICATIONS

- General Purpose Amplification.

SOT - 323


1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-150	mA
P_C	Collector Power Dissipation	100	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	1250	$^{\circ}\text{C}/\text{W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-100	nA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-2\text{mA}$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$			-0.3	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			7	pF

CLASSIFICATION OF h_{FE}

RANK	O	Y	GR(G)
RANGE	70 - 140	120 - 240	200 - 400
MARKING	SO	SY	SG